Arthur F Hebard

List of Publications by Year
in descending order

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184	21,020	25034	9103
papers	citations	57	144
		h-index	g-index

184	184	184	17317
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Asymmetric Design of Spin-Crossover Complexes to Increase the Volatility for Surface Deposition. Journal of the American Chemical Society, 2021, 143, 14563-14572.	13.7	16
2	Far-infrared absorption of undoped and Br-doped carbon nanofiber powder in stacked-cup cone configuration. Physical Review B, 2020, 102, .	3.2	1
3	Characteristics of Single-Molecule Magnet Dimers ([Mn₃]₂) on Graphene and h-BN. Journal of Physical Chemistry C, 2020, 124, 28186-28200.	3.1	11
4	Electronegative ligands enhance charge transfer to Mn12 single-molecule magnets deposited on graphene. Journal of Applied Physics, 2020, 127, 064303.	2.5	8
5	Chelation-assisted assembly of multidentate colloidal nanoparticles into metalâ€“organic nanoparticles. Nanoscale, 2018, 10, 21369-21373.	5.6	2
6	Improved memristive switching of graphite/Nb:SrTiO 3 interfaces by tuning Fermi levels and dielectric constants. Journal of Applied Physics, 2018, 124, 152120.	2.5	0
7	Enhancement of ferromagnetism in BaFeO 3 â€KTa 0.47 Nb 0.53 O 3 multilayers compared to pseudoâ€cubic BaFeO 3 thin film grown by pulsed laser deposition. Physica Status Solidi (A) Applications and Materials Science, 2017, 214, 1600707.	1.8	1
8	Detection of charge density wave phase transitions at 1T-TaS2/GaAs interfaces. Applied Physics Letters, 2017, 110, 181603.	3.3	7
9	van der Waals Schottky barriers as interface probes of the correlation between chemical potential shifts and charge density wave formation in <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>1</mml:mn><mml:mi>T</mml:mi><mml:mtext>â^’</mml:m and <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mn>2</mml:mn><mml:mi>H</mml:mi><mml:mtext>â^’</mml:m Physical Review B, 2017, 96, .	3.2	5
10	Bi-2212/1T-TaS2 Van der Waals junctions: Interplay of proximity induced high-T c superconductivity and CDW order. Scientific Reports, 2017, 7, 4639.	3.3	7
11	Optimization of atomically smooth and metallic surface of SrTiO3. Journal of Applied Physics, 2017, 121, .	2.5	4
12	Strain induced enhancement of magnetization in Ba2FeMoO6 based heterostructure with (BaxSr1-x)TiO3. Journal of Applied Physics, 2016, 119, .	2.5	3
13	Superlattice periodicity and magnetic properties of Ba2FeMoO6/Ba0.5Sr0.5TiO3 system. Journal of Applied Physics, 2016, 119, 215303.	2.5	5
14	Synthesis of graphene and graphene nanostructures by ion implantation and pulsed laser annealing. Journal of Applied Physics, 2016, 120, .	2.5	4
15	Moderately-doped Schottky barriers: a description using thermionic emission over a wide temperature range. Journal Physics D: Applied Physics, 2016, 49, 455101.	2.8	3
16	Proximate transition temperatures amplify linear magnetoelectric coupling in strain-disordered multiferroic<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>BiMnO</mml:mi><mml:mn>3</mml:mn></mml:msub></ Physical Review B, 2016, 93, .	3.2	11
17	The effects of oxygen pressure on disordering and magneto-transport properties of Ba2FeMoO6 thin films grown via pulsed laser deposition. Journal of Applied Physics, 2015, 118, 033903.	2.5	4
18	Orientational strain modulation of ferroelectric polarization in multiferroic BiMnO3. Applied Physics Letters, 2014, 105, .	3.3	3

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19	Unusual Shubnikovâ€“de Haas oscillations in BiTeCl. Physical Review B, 2014, 90, .	3.2	15
20	Fe doped CdTeS magnetic quantum dots for bioimaging. Journal of Materials Chemistry B, 2013, 1, 6312.	5.8	18
21	Measurement of the polarization vector in BiMnO3 multiferroic thin films using surface and embedded microelectrodes. Journal of Applied Physics, 2013, 114, 094104.	2.5	2
22	Bulk Fermi surface and electronic properties of Cu0.07Bi2Se3. Physical Review B, 2013, 87, .	3.2	14
23	Superparamagnetic Nanocomposites Templated with Pyrazole-Containing Diblock Copolymers. Polymers, 2012, 4, 1211-1225.	4.5	7
24	Magnetic properties of MoS2: Existence of ferromagnetism. Applied Physics Letters, 2012, 101, .	3.3	249
25	Magnetic and magnetotransport properties of Ba2FeMoO6 pulsed laser deposited thin films. Journal of Applied Physics, 2012, 112, .	2.5	9
26	Unusual metalâ€“insulator transition in disordered ferromagnetic films. Physica B: Condensed Matter, 2012, 407, 4023-4026.	2.7	1
27	Competing soft dielectric phases and detailed balance in thin film manganites. Physical Review B, 2012, 86, .	3.2	3
28	Rectification at Graphene-Semiconductor Interfaces: Zero-Gap Semiconductor-Based Diodes. Physical Review X, 2012, 2, .	8.9	137
29	Strain-induced suppression of weak localization in CVD-grown graphene. Journal of Physics Condensed Matter, 2012, 24, 475304.	1.8	5
30	Drawing graphene nanoribbons on SiC by ion implantation. Applied Physics Letters, 2012, 100, .	3.3	37
31	Current transport across the pentacene/CVD-grown graphene interface for diode applications. Journal of Physics Condensed Matter, 2012, 24, 255802.	1.8	30
32	Low-temperature, site selective graphitization of SiC via ion implantation and pulsed laser annealing. Applied Physics Letters, 2012, 100, .	3.3	19
33	High Efficiency Graphene Solar Cells by Chemical Doping. Nano Letters, 2012, 12, 2745-2750.	9.1	861
34	Extinction of ferromagnetism in highly ordered pyrolytic graphite by annealing. Carbon, 2012, 50, 1614-1618.	10.3	21
35	Growth and characterization of multiferroic BiMnO3 thin films. Journal of Applied Physics, 2011, 109, .	2.5	45
36	Graphene/GaN Schottky diodes: Stability at elevated temperatures. Applied Physics Letters, 2011, 99, 102102.	3.3	111

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37	Built-in and induced polarization across LaAlO3/SrTiO3 heterojunctions. Nature Physics, 2011, 7, 80-86.	16.7	178
38	Ultrapure multilayer graphene in bromine-intercalated graphite. Physical Review B, 2011, 84, .	3.2	16
39	Stable hole doping of graphene for low electrical resistance and high optical transparency. Nanotechnology, 2011, 22, 425701.	2.6	163
40	Magnetically Driven Single DNA Nanomotor. Small, 2011, 7, 601-605.	10.0	12
41	Finite size effects with variable range exchange coupling in thin-film Pd/Fe/Pd trilayers. Journal of Magnetism and Magnetic Materials, 2010, 322, 2618-2621.	2.3	9
42	A collective dynamics description of dipolar interactions and the coercive field of magnetic nanoparticles. Journal of Applied Physics, 2010, 108, 123920.	2.5	8
43	Supermetallic conductivity in bromine-intercalated graphite. Physical Review B, 2010, 81, .	3.2	76
44	Intrinsic Tunneling in Phase Separated Manganites. Physical Review Letters, 2009, 102, 077205.	7.8	63
45	Tunneling magnetoresistance in phase-separated manganite nanobridges. Physical Review B, 2009, 80, .	3.2	31
46	Magnetodielectric coupling in nonmagnetic Au/GaAs:Si Schottky barriers. Physical Review B, 2009, 80, .	3.2	10
47	Graphite in the bilayer regime: In-plane transport. Physical Review B, 2009, 80, .	3.2	6
48	Block Copolymer-Mediated Formation of Superparamagnetic Nanocomposites. Chemistry of Materials, 2009, 21, 5644-5653.	6.7	20
49	Graphite based Schottky diodes formed on Si, GaAs, and 4H-SiC substrates. Applied Physics Letters, 2009, 95, .	3.3	140
50	Dipolar interactions and their influence on the critical single domain grain size of Ni in layered Ni/Al₂O₃composites. Journal of Physics Condensed Matter, 2008, 20, 385213.	1.8	9
51	Phase Transitions of Dirac Electrons in Bismuth. Science, 2008, 321, 547-550.	12.6	150
52	Magnetization dependence on carrier doping in epitaxial ZnO thin films co-doped with Mn and P. Journal of Applied Physics, 2007, 101, 123909.	2.5	40
53	Colossal magnetocapacitance and scale-invariant dielectric response in phase-separated manganites. Nature Physics, 2007, 3, 551-555.	16.7	56
54	ZnO spintronics and nanowire devices. Journal of Electronic Materials, 2006, 35, 862-868.	2.2	148

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55	Synthesis and magnetic characterization of microstructures prepared from microbial templates of differing morphology. Materials Letters, 2006, 60, 19-22.	2.6	18
56	Metal-Insulator-Like Behavior in Semimetallic Bismuth and Graphite. Physical Review Letters, 2005, 94, 166601.	7.8	179
57	Magnetization dependence on electron density in epitaxial ZnO thin films codoped with Mn and Sn. Journal of Applied Physics, 2005, 97, 053904.	2.5	73
58	Spatial distribution and electronic state of Co in epitaxial anatase CoxTi1â^'xO2 thin films grown by reactive sputtering. Applied Physics Letters, 2004, 84, 2608-2610.	3.3	62
59	Ferromagnetic AlGaCrP Films by Ion Implantation. Electrochemical and Solid-State Letters, 2004, 7, G44.	2.2	1
60	Transparent, Conductive Carbon Nanotube Films. Science, 2004, 305, 1273-1276.	12.6	2,797
61	Wide bandgap GaN-based semiconductors for spintronics. Journal of Physics Condensed Matter, 2004, 16, R209-R245.	1.8	117
62	Effects of High Dose Ni, Fe, Co, and Mn Implantation into SnO[sub 2]. Electrochemical and Solid-State Letters, 2004, 7, G309.	2.2	21
63	Mining for highTcferromagnetism in ion-implanted dilute magnetic semiconductors. Journal Physics D: Applied Physics, 2004, 37, 511-517.	2.8	72
64	Effects of high-dose Mn implantation into ZnO grown on sapphire. Applied Physics Letters, 2004, 84, 2292-2294.	3.3	167
65	Growth of the dilute magnetic semiconductor GaMnN by molecular-beam epitaxy. Journal of Electronic Materials, 2003, 32, 298-306.	2.2	10
66	Coexistence of glassy antiferromagnetism and giant magnetoresistance in Fe/Cr multilayer structures. Journal of Magnetism and Magnetic Materials, 2003, 263, 32-37.	2.3	7
67	Room temperature ferromagnetism in GaMnN and GaMnP. Physica Status Solidi A, 2003, 195, 222-227.	1.7	19
68	Wide band gap ferromagnetic semiconductors and oxides. Journal of Applied Physics, 2003, 93, 1-13.	2.5	987
69	Ferromagnetism in Mn-implanted ZnO:Sn single crystals. Applied Physics Letters, 2003, 82, 239-241.	3.3	403
70	Transition metal ion implantation into AlGaN. Journal of Applied Physics, 2003, 94, 4956.	2.5	23
71	Large magnetoresistance of bismuth/gold films thermally deposited onto glass substrates. Applied Physics Letters, 2003, 82, 2293-2295.	3.3	18
72	Ferromagnetic semiconductors based upon AlGaP. Journal of Applied Physics, 2003, 93, 7861-7863.	2.5	9

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73	Magnetic scattering in Feâ€“Cr multilayers in the ferromagnetic state at low temperatures. Journal of Applied Physics, 2003, 93, 7684-7686.	2.5	6
74	Magnetocapacitance: Probe of Spin-Dependent Potentials. Physical Review Letters, 2003, 90, 117201.	7.8	39
75	Contribution of interface capacitance to the electric-field breakdown in thin-film Alâ€“AlOxâ€“Al capacitors. Applied Physics Letters, 2003, 83, 2417-2419.	3.3	13
76	Properties of Co-, Cr-, or Mn-implanted AlN. Journal of Applied Physics, 2003, 94, 1592-1596.	2.5	58
77	Effects of hydrogen incorporation in GaMnN. Applied Physics Letters, 2003, 83, 5458-5460.	3.3	18
78	Hydrogenation Effects on Magnetic Properties of GaMnP. Electrochemical and Solid-State Letters, 2003, 6, G131.	2.2	10
79	Magnetic and structural characterization of Mn-implanted, single-crystal ZnGeSiN2. Journal of Applied Physics, 2002, 92, 2047-2051.	2.5	43
80	Use of ion implantation to facilitate the discovery and characterization of ferromagnetic semiconductors. Journal of Applied Physics, 2002, 91, 7499.	2.5	63
81	Unconventional Carrier-Mediated Ferromagnetism above Room Temperature in Ion-Implanted (Ga,) Tj ETQq1 1 0.784314 rgBT /Overlo	7.8	214
82	Magnetism in SiC implanted with high doses of Fe and Mn. Journal of Electronic Materials, 2002, 31, 336-339.	2.2	10
83	Magnetic effects of direct ion implantation of Mn and Fe into p-GaN. Journal of Electronic Materials, 2002, 31, 411-415.	2.2	4
84	Synthesis and Characterization of Silica-Coated Iron Oxide Nanoparticles in Microemulsion:â€‰ The Effect of Nonionic Surfactants. Langmuir, 2001, 17, 2900-2906.	3.5	732
85	Magnetic and structural properties of Mn-implanted GaN. Applied Physics Letters, 2001, 78, 3475-3477.	3.3	268
86	Nanoscale Magnetic Regions Formed in GaN Implanted with Mn. Journal of Nanoscience and Nanotechnology, 2001, 1, 101-106.	0.9	22
87	Ion Beam Deposited Gmr Materials. Materials Research Society Symposia Proceedings, 2001, 690, F9.12.1.	0.1	2
88	Epitaxial Growth of Dilute Magnetic Semiconductors: GaMnN and GaMnP. Materials Research Society Symposia Proceedings, 2001, 674, 1.	0.1	3
89	Ferromagnetic and Paramagnetic Semiconductors Based upon GaN, AlGaN, and GaP. Materials Research Society Symposia Proceedings, 2001, 690, F1.5.1.	0.1	2
90	Ferromagnetic and Structural Properties of Mn-Implanted p-GaN. Materials Research Society Symposia Proceedings, 2001, 674, 1.	0.1	1

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91	Magnetic Properties of Fe- and Mn-Implanted SiC. Electrochemical and Solid-State Letters, 2001, 4, G119.	2.2	47
92	Characterization of high dose Fe implantation into p-GaN. Applied Physics Letters, 2001, 79, 3452-3454.	3.3	54
93	Unambiguous determination of thegfactor for holes in bismuth at highB/T. Physical Review B, 2001, 64, .	3.2	28
94	Indication of ferromagnetism in molecular-beam-epitaxy-derived N-type GaMnN. Applied Physics Letters, 2001, 79, 1312-1314.	3.3	268
95	Magnetic properties of P-type GaMnP grown by molecular-beam epitaxy. Applied Physics Letters, 2001, 79, 3128-3130.	3.3	45
96	Charge Transfer and the Route to Superconductivity in the Doped Fullerenes. Journal of Superconductivity and Novel Magnetism, 2000, 13, 829-831.	0.5	1
97	Ultrafast dynamics of superconductingK3C60andRb3C60. Physical Review B, 2000, 62, 1366-1378.	3.2	6
98	Spin-Peierls transition inNaV2O5in high magnetic fields. Physical Review B, 2000, 61, R13321-R13324.	3.2	14
99	Carbon nanotube-modified cantilevers for improved spatial resolution in electrostatic force microscopy. Applied Physics Letters, 1999, 75, 2842-2844.	3.3	29
100	Bad-Metal Behavior: Exotic Physics or a Consequence of Microstructure?. Journal of Superconductivity and Novel Magnetism, 1999, 12, 159-162.	0.5	3
101	Frequency-dependent interface capacitance of Alâ€“Al2O3â€“Al tunnel junctions. Applied Physics Letters, 1999, 74, 302-304.	3.3	32
102	Anomalous 4He Adsorption to in situ Baked C60. Journal of Low Temperature Physics, 1998, 113, 453-458.	1.4	3
103	Thin Film Adsorption of 4He To C60. Journal of Low Temperature Physics, 1998, 110, 647-652.	1.4	3
104	Bad Metals Made with Good-Metal Components. Physical Review Letters, 1998, 81, 3936-3939.	7.8	40
105	Role of molecular oxygen and other impurities in the electrical transportand dielectric properties ofC60films. Physical Review B, 1997, 55, 16439-16449.	3.2	99
106	Coherent phonons in alkali metal-doped C60. Applied Physics Letters, 1997, 71, 2734-2736.	3.3	24
107	4He Adsorption and Superfluid Transition on C60. Journal of Low Temperature Physics, 1997, 109, 243-265.	1.4	5
108	A search for4He in C60 interstitial sites. European Physical Journal D, 1996, 46, 421-422.	0.4	1

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109	Charge transfer and surface scattering at Cu-C60planar interfaces. Physical Review B, 1996, 54, 14052-14060.	3.2	41
110	Phototransformation in visible and nearâ€IR femtosecond pumpâ€probe studies of C60 films. Applied Physics Letters, 1996, 69, 296-298.	3.3	18
111	Structural and electronic properties of(NH3)xK3C60. Physical Review B, 1995, 52, 483-489.	3.2	62
112	C60 thin film transistors. Applied Physics Letters, 1995, 67, 121-123.	3.3	546
113	Materials with a Buried â€‰Câ€‰60 Layer Produced by Direct Wafer Bonding. Journal of the Electrochemical Society, 1994, 141, L137-L138.	2.9	9
114	Plasmon Fine Structures in Multiple Inelastic Electron Scattering off C ₆₀ Crystallites. Europhysics Letters, 1994, 27, 519-524.	2.0	2
115	Ultrasonic investigation of amorphous superconducting films. Physical Review B, 1994, 50, 3988-3994.	3.2	1
116	Charge transfer at aluminum-C60interfaces in thin-film multilayer structures. Physical Review B, 1994, 50, 17740-17743.	3.2	59
117	New Phases of C60 Synthesized at High Pressure. Science, 1994, 264, 1570-1572.	12.6	657
118	Fermi-liquid behavior in the electrical resistivity ofK3C60andRb3C60. Physical Review B, 1994, 50, 3462-3465.	3.2	37
119	Fabrication and Properties of Free-Standing C60 Membranes. Science, 1993, 259, 1887-1890.	12.6	39
120	Doping-induced spectral evolution inC60: Evidence of immiscible stoichiometric phases inAxC60(A=K,Rb;x=0, 3, and 6) thin films. Physical Review B, 1993, 48, 2738-2742.	3.2	14
121	Buckminsterfullerene. Annual Review of Materials Research, 1993, 23, 159-191.	5.5	87
122	Absence of saturation in the normal-state resistivity of thin films ofK3C60andRb3C60. Physical Review B, 1993, 48, 9945-9948.	3.2	86
123	4He superfluidity on hydrogen and C60. Journal of Physics Condensed Matter, 1992, 4, 9525-9530.	1.8	0
124	Low-temperature insulating phases of uniformly disordered two-dimensional superconductors. Physical Review Letters, 1992, 69, 1604-1607.	7.8	169
125	Field and Hall effects in semiconductingYBa2Cu3O6+Î´. Physical Review B, 1992, 46, 520-523.	3.2	12
126	Electronic transport properties ofK3C60films. Physical Review Letters, 1992, 68, 1054-1057.	7.8	140

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127	Infrared spectroscopy through the orientational phase transition in fullerene films. Physical Review B, 1992, 46, 2591-2594.	3.2	45
128	Electrical Resistivity and Stoichiometry of Kkhgr C60 Films. Science, 1992, 255, 184-186.	12.6	114
129	Electrical Resistivity and Stoichiometry of CaxC60 and SrxC60 Films. Science, 1992, 258, 1636-1638.	12.6	58
130	Third sound and mass adsorption studies of4He on C60. Journal of Low Temperature Physics, 1992, 89, 609-612.	1.4	9
131	Transport properties ofAl65Cu15Co20andAl70Ni15Co15decagonal quasicrystals. Physical Review Letters, 1991, 67, 719-722.	7.8	85
132	Photoemission Spectra and Electronic Properties of KxC60. Science, 1991, 252, 1419-1421.	12.6	158
133	Raman Studies of Alkali-Metal Doped AxC60 Films (A = Na, K, Rb, and Cs; x = 0, 3, and 6). Science, 1991, 254, 1625-1627.	12.6	196
134	Deposition and characterization of fullerene films. Applied Physics Letters, 1991, 59, 2109-2111.	3.3	337
135	Conducting films of C60 and C70 by alkali-metal doping. Nature, 1991, 350, 320-322.	27.8	1,057
136	Superconductivity at 18 K in potassium-doped C60. Nature, 1991, 350, 600-601.	27.8	2,964
137	Photoelectrochemical behavior of C60 films. Journal of the American Chemical Society, 1991, 113, 6291-6293.	13.7	127
138	Cation termination at ionâ€polished and chemically etched (001)YBa2Cu3O7crystal surfaces: An ion channeling study. Applied Physics Letters, 1991, 58, 777-779.	3.3	11
139	Ultrasonic investigation of granular superconducting films. Physical Review B, 1991, 43, 505-513.	3.2	6
140	Vortex-pair nucleation at defects: A mechanism for anomalous temperature dependence in the superconducting screening length. Physical Review B, 1991, 44, 9753-9756.	3.2	25
141	Fioryet al. reply. Physical Review Letters, 1991, 67, 3196-3196.	7.8	11
142	Correlation of structural quality with superconducting behavior in epitaxial thin films of Ba2YCu3O7â˜Îon LaAlO3(100). Journal of Applied Physics, 1991, 70, 4982-4988.	2.5	34
143	Superconductivity at 28 K inRbxC60. Physical Review Letters, 1991, 66, 2830-2832.	7.8	848
144	Hierarchically occupied pinning distributions and vortex transport in superconductors. Physical Review B, 1991, 43, 6253-6256.	3.2	13

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145	Metallic and superconducting surfaces ofYBa2Cu3O7probed by electrostatic charge modulation of epitaxial films. Physical Review Letters, 1990, 65, 3441-3444.	7.8	153
146	Anomalous tunneling into superconductinga-InOxfilms. Physical Review Letters, 1990, 65, 666-666.	7.8	2
147	Magnetic-field-tuned superconductor-insulator transition in two-dimensional films. Physical Review Letters, 1990, 65, 927-930.	7.8	473
148	Pair-breaking description of the vortex-depinning critical field inYBa2Cu3O7thin films. Physical Review B, 1989, 40, 5243-5246.	3.2	64
149	Magnetic penetration depth ofYBa2Cu3O7. Physical Review Letters, 1989, 62, 2885-2885.	7.8	26
150	Nonlinear temperature dependence of the normal-state resistivity inYBa2Cu4O8Â±Î´films. Physical Review B, 1989, 39, 9611-9613.	3.2	82
151	Mechanical measurements of two-dimensional flux lattices: Observation of two-stage melting. Physical Review B, 1989, 40, 7354-7356.	3.2	7
152	Possibility of the vortex-antivortex transition temperature of a thin-film superconductor being renormalized by disorder. Physical Review B, 1989, 39, 4105-4109.	3.2	12
153	Ion beam thinning and polishing of YBa2Cu3O7films. Applied Physics Letters, 1989, 55, 1915-1917.	3.3	44
154	Penetration depths of highTcfilms measured by twoâ€coil mutual inductances. Applied Physics Letters, 1988, 52, 2165-2167.	3.3	191
155	Flux-Lattice Melting in Amorphous CompositeInInOxTwo-Dimensional Superconductors. Physical Review Letters, 1988, 60, 144-147.	7.8	62
156	Magnetization measurements of single levitated grains of Ba2YCu3O7. Applied Physics Letters, 1988, 53, 2238-2240.	3.3	13
157	Observation of a halide (F/Cl) stabilized, new perovskite phase in superconducting Y2Ba5Cu7Oxfilms. Applied Physics Letters, 1988, 52, 1625-1627.	3.3	46
158	Renormalization of the Mean-Field Superconducting Penetration Depth in Epitaxial YBa2Cu3O7Films. Physical Review Letters, 1988, 61, 1419-1422.	7.8	272
159	Interface contribution to the capacitance of thinâ€film Alâ€Al2O3â€Al trilayer structures. Applied Physics Letters, 1987, 51, 1349-1351.	3.3	34
160	Microstructure, dimensionality, and depression of the transition temperature in disordered superconducting films. Physical Review Letters, 1987, 58, 1131-1134.	7.8	19
161	Magnetoconductance of thin-film superconductors near critical disorder. Physical Review B, 1986, 33, 1691-1699.	3.2	31
162	Oxygenâ€rich polycrystalline magnesium oxideâ€”A high quality thinâ€film dielectric. Applied Physics Letters, 1986, 48, 520-522.	3.3	15

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163	Diverging Characteristic Lengths at Critical Disorder in Thin-Film Superconductors. Physical Review Letters, 1985, 54, 2155-2158.	7.8	49
164	Pair-breaking model for disorder in two-dimensional superconductors. Physical Review B, 1984, 30, 4063-4066.	3.2	115
165	A criterion for the determination of upper critical fields in highly disordered thinâ€film superconductors. Applied Physics Letters, 1984, 45, 794-796.	3.3	14
166	Electron Mobility, Conductivity, and Superconductivity near the Metal-Insulator Transition. Physical Review Letters, 1984, 52, 2057-2060.	7.8	70
167	Optical recording applications of reactive ion beam sputter deposited thinâ€film composites. Applied Physics Letters, 1984, 44, 1023-1025.	3.3	12
168	Critical-Exponent Measurements of a Two-Dimensional Superconductor. Physical Review Letters, 1983, 50, 1603-1606.	7.8	119
169	Superconducting phase transitions in indium/indium-oxide thin-film composites. Physical Review B, 1983, 28, 5075-5087.	3.2	216
170	Systematics of the dielectric constant of vortex phases in superconducting films. Physical Review B, 1982, 25, 2073-2076.	3.2	18
171	Structural phase transitions of indium/indium oxide thinâ€film composites. Applied Physics Letters, 1982, 41, 1130-1132.	3.3	60
172	Structural aspects of tunnelâ€junction coupled granular lead films. Journal of Vacuum Science and Technology, 1981, 18, 268-272.	1.9	15
173	Role of Clusters in the Approach to Localization of Josephson-Coupled Granular Lead Films. Physical Review Letters, 1980, 44, 50-54.	7.8	46
174	Evidence for the Kosterlitz-Thouless Transition in Thin Superconducting Aluminum Films. Physical Review Letters, 1980, 44, 291-294.	7.8	198
175	Thermal time constants of thinâ€film resistors using pulse nonlinearity measurements. Journal of Applied Physics, 1978, 49, 5250-5255.	2.5	9
176	Diagnostics with seriesâ€connected Josephson tunnel junctions. Journal of Applied Physics, 1978, 49, 338-343.	2.5	17
177	Evidence for chemical annealing effects in indium oxide tunnelâ€junction barriers. Journal of Applied Physics, 1978, 49, 6039-6044.	2.5	9
178	Critical currents associated with the interaction of commensurate fluxâ€line sublattices in a perforated Al film. Applied Physics Letters, 1978, 32, 73-75.	3.3	200
179	Evidence for the Existence of Fractional Charge on Matter. Physical Review Letters, 1977, 38, 1011-1014.	7.8	141
180	Observation of dissipation asymmetries in tunnel junctions at high bias. Physical Review B, 1976, 14, 1751-1757.	3.2	5

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181	Josephson Junctions in Transverse Magnetic Fields. Physical Review Letters, 1975, 35, 1310-1311.	7.8	13
182	A new approach to high resolution measurements of structure in superconducting tunneling currents. Review of Scientific Instruments, 1974, 45, 529-533.	1.3	37
183	A Superconducting Suspension with Variable Restoring Force and Low Damping. Review of Scientific Instruments, 1973, 44, 425-429.	1.3	14
184	Tunneling Studies of the Formation of Intermetallic Compounds in Goldâ€“Lead Films. Journal of Vacuum Science and Technology, 1973, 10, 606-610.	1.9	13